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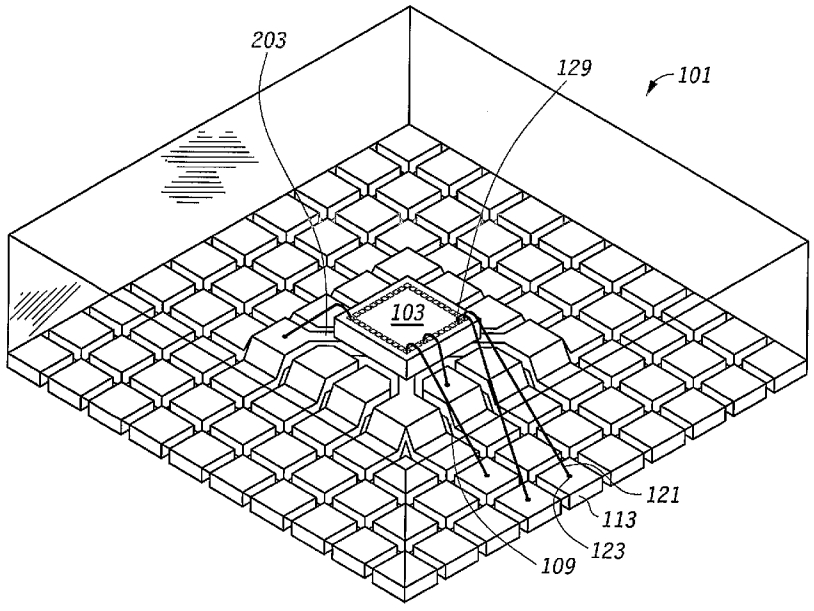
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(54) Title: MULTI-DIE SEMICONDUCTOR PACKAGE



(57) Abstract: A multi-die semiconductor package (101) having an electrical interconnect frame (107). A top integrated circuit die (103) is attached to the top side of an upper contact level (109) of the frame and a bottom integrated circuit die (105) is attached to the bottom side of the upper contact level of the frame. The die bond pads (113) of the top die are electrically coupled (e.g. wired bonded) to pads of a lower contact level (111) of the interconnect frame. The die bond pads of the bottom integrated circuit die are electrically coupled (e.g. wired bonded) to bond pads of the upper contact level of the frame. The bond pads of the lower contact level serve as external bond pads for the package. The frame may include inset structures (116), each having an upper portion located in the upper contact level and a lower portion located in the lower contact level.

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